



## DOCUMENT CHANGE REQUEST

DCR number 1264

Changes required for: Qualification

Originator: Valerie Lepaludier

Date: 2019/07/04

Date sent: 2019/04/26

Organisation: Atmel Microchip

Status: IMPLEMENTED

Title: INTEGRATED CIRCUITS, SILICON MONOLITHIC, CMOS, CELL-BASED ARRAY BASED ON TYPE

Number: 9202/083

Issue: 2

Other documents affected:

Page:

All  
For all modifications/corrections requested, see document attached.

Paragraph:

§1.4.2  
§1.6  
§1.7  
§ 2.3.1

Original wording:

1. MQFP and MCGA packages
2. Component type variant in §1.4.2
3. handling precautions : minimum path failure of 1000V in §1.6
4. physical dimensions and terminal identification in §1.7
5. Electrical table §2.3.1

Proposed wording:

- For all modifications requested, see document attached.
1. CQFP and CCGA packages
  2. new variants from 75 to 114
  3. §1.6 handling precautions : minimum path failure of 500V
  4. see attached document for package drawing
  5. see attached document for corrections

Justification:

1. Change of wording: all references to MQFP and MCGA packages shall be replaced by CQFP and CCGA packages
2. introduction of new die size and packages
3. Correction
4. new packages added
5. Parameters not specified in the table, but read and recorded



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Justification:

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Attachments:

modifs\_9202083\_issue\_2.doc

Modifications:

Regarding 3-digit Component Type variant Numbers ESA has verified that they could accept three digit variants (ref email from Fernando Martinez dated 1st July 2019) Therefore this open point is considered closed.

Following further email correspondence with the manufacturer, the Technical writer has updated the Detail Spec. the applicable Low and High level Drift value limits to CMOS buffers and LVDS buffers ( para. 2.4 Parameter Drift Values) should be different ie 10% of the absolute limits for IIL/IIH and this had been omitted from 9202/083 Draft 3A see attached Draft 3b

Approval signature:

Date signed:

2019-07-04